

# Stopping for Ion : **H** , Target = **Si**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1962</b>	Ewing, R. I. 'Response of Silicon Surface Barrier Detectors to Hydrogen Ions of Energies 25 to 250 keV' <i>IEEE Trans. Nucl. Sci., NS-09, No. 3, 207-10 (1962)</i> <i>Comment : S. Rel. To H+. (70 keV/amu) H+2, H+3 -&gt; Si</i>	1962-Ewin 0513
<b>1964</b>	Dearnaley, G. 'The Channeling of Ions through Silicon Detectors' <i>IEEE Trans. Nucl. Sci., NS-11, 249-53 (1964)</i> <i>Comment : S, dS. 2 MeV H -&gt; Si (Cryst.)</i>	1964-Dear 0171
<b>1964</b>	Erginsoy, C. Wegner, H. E. Gibson, W. M. 'Anisotropic Energy Loss of Light Particles of MeV Energies in Thin Silicon Single Crystals' <i>Phys. Rev. Letters, 13, 530-34 (1964)</i> <i>Comment : S, dS. 2.8 MeV H -&gt; Si (Cryst.)</i>	1964-Ergi 0189
<b>1965</b>	Appleton, B. R. Erginsoy, C. Wegner, H. E. Gibson, W. M. 'Axial and Planar Effects in the Energy Loss of Protons in Silicon Single Crystals' <i>Phys. Letters, 19, 185-86 (1965)</i> <i>Comment : S, dS. 4.85 MeV H -&gt; Si (Cryst.)</i>	1965-Appl 0224
<b>1965</b>	Grew, G. W. 'Cyclotron Tests to Determine the Response of Solid-State Detectors to Protons of Energies 50 to 160 MeV for Use in a Proton Spectrometer' <i>IEEE Trans. Nucl. Sci., NS-12, 308-13 (1965)</i> <i>Comment : S, dS. 50-160 MeV H -&gt; Si</i>	1965-Grew 0515
<b>1965</b>	Wegner, H. E. Appleton, B. R. Erginsoy, C. Gibson, W. M. 'Axial and Planar Effects in the Energy Loss of Protons in Silicon Single Crystals' <i>Phys. Letters, 19, 187-89 (1965)</i> <i>Comment : S, dS. 4.85 MeV H -&gt; Si (Cryst.)</i>	1965-Wegn 0595
<b>1966</b>	Appleton, B. R. Altman, M. Feldman, L. C. Gibson, W. M. Erginsoy, C. 'Least Energy Loss and Its Dispersion for $\beta$ Channeled $\beta$ Protons in Silicon and Germanium Single Crystals' <i>Bull. Am. Phys. Soc., 11, 176 (1966)</i> <i>Comment : S, dS. 3-11 MeV H -&gt; Si, Ge (Both Cryst.)</i>	1966-Appl 0257
<b>1966</b>	Eisen, F. H. 'Channeling of 375 keV Protons through Silicon' <i>Phys. Letters, 23, 401-02 (1966)</i> <i>Comment : S, dS. 375 keV H -&gt; Si (Cryst.)</i>	1966-Eise 0275

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<b>1966</b>	Lander, R. L. Mehlhop, W. A. Lubatti, H. J. Schnurmacher, G. L. 'Solid-State Devices as Detectors of High-Energy Interactions' <i>Nucl. Inst. Methods, 42, 261-68 (1966)</i> <i>Comment : dS. 760 MeV H -&gt; Si</i>	<b>1966-Land</b> 0423
<b>1967</b>	Remillieux, J. Samuelli, J. J. Sarazin, A. 'Etude Des Effets Directionnels Dans La Transmission De Protons De 2 MeV a Travers Un Monocristal De Silicium' <i>J. Physique, 28, 832-38 (1967)</i> <i>Comment : S, dS. 2 MeV H -&gt; Si (Cryst.)</i>	<b>1967-Remi</b> 0602
<b>1968</b>	Mannami, M. Fujimoto, F. Ozawa, K. 'Anomalous Energy Losses of 1.5 MeV Protons Channeled in Silicon Single Crystals.' <i>Phys. Letters A, 26, 201-02 (1968)</i> <i>Comment : S, dS. 1.5 MeV H -&gt; Si (Cryst.)</i>	<b>1968-Mann</b> 0320
<b>1968</b>	Sattler, A. R. Dearnaley, G. 'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si' <i>Phys. Rev., 161, 244-52 (1967)(Erratum, Phys. Rev., 165, 750 (1968))</i> <i>Comment : S. 4-7.6 MeV H, D -&gt; Ge, GaAs, Si (All Cryst.)</i>	<b>1968-Satt</b> 0308
<b>1968</b>	Shipatov, E. T. Kononov, B. A. 'Investigation of the Channeling of Protons in Single Crystals of Ionic Compounds and Semiconductors' <i>Izv. Vuz. Fiz. No. 9, 52-56 (1968). [Engl. Trans. Soviet Phys. J. No. 9, 46-49, (1968)]</i> <i>Comment : S,dS. H (4.7-6.7 MeV) -&gt; NaCl, KCl, KBr, Si, Ge (crystals)</i>	<b>1968-Ship2</b> 0599
<b>1968</b>	Shipatov, E. T. Kononov, B. A. 'Energy Distribution of 6.72 MeV Protons Passing through Monocrystals.' <i>Atomnaya Energiya (USSR), 25, 439-40 (1968) [Engl. Trans. Sov. Atom. Energy, 25, 1254-55 (1968).</i> <i>Comment : S, dS. 6.72 MeV H -&gt; NaCl, KCl, KBr, Si, Ge (All Cryst.)</i>	<b>1968-Ship3</b> 0653
<b>1969</b>	Aitken, D. W. Lakin, W. L. Zulliger, H. R. 'Energy Loss and Straggling in Silicon by High-Energy Electrons, Positive Pions, and Protons' <i>Phys. Rev., 179, 393-98 (1969)</i> <i>Comment : S, dS. 29-300 MeV H, 50-200 MeV Pi+ -&gt; Si</i>	<b>1969-Aitk</b> 0385
<b>1969</b>	Arkhipov, E. P. Gott, Yu. V. 'Slowing Down of 0.5 - 30 keV Protons in Some Materials.' <i>Zh. Eksp. Teor. Fiz., 56, 1146-51 (1969). [Engl. Trans. Sov. Phys. JETP, 29, 615-18 (1969)</i> <i>Comment : S. 0.5-30 keV H -&gt; C, Ti, Al, Cu, Ni, Fe, Ge, Si, Sb, Bi</i>	<b>1969-Arkh</b> 0410

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1969	Clark, G. J. Dearnaley, G. Morgan, D. V. Poate, J. M. 'The Stopping Power of Protons Channelled through Csi Crystals' <i>Phys. Letters A</i> , 30, 11-12 (1969) <i>Comment</i> : S. 4 MeV H -> Si (Cryst.)	1969-Clar 0127
1969	Shipatov, E. T. 'Energy and Angular Distributions of Protons Transmitted by Germanium and Silicon Single Crystals Along (110) and (100) Channels in the Crystal Lattice' <i>Fiz. Tekh. Poluprovodnikov</i> , 2, 1690-91 (1968). [ <i>Engl. Trans. Sov. Phys. Semicond.</i> , 2, 1408-09 (1969)] <i>Comment</i> : S, dS. 6.72 MeV H -> Si, Ge (Both Cryst.)	1969-Ship2 0654
1970	Kononov, B. A. Struts, V. K. 'Channeling of Protons in Silicon at Different Temperatures' <i>Izv. Vuz. Fiz. No. 6</i> , 60-63 (1970). [ <i>Engl. Trans. Sov. Phys. J.</i> , 13, 738-61 (1970)] <i>Comment</i> : S, dS. 6.72 MeV H -> Si (Cryst.)	1970-Kono 0646
1971	Chemin, J. F. Roturier, J. Petit, G. Y. 'Mesure par Reactions Nucleaires Resonnantes du Relentissement et de la Dispersion en Energie de Protons' <i>J. Phys. (Paris)</i> , 32, 220 (1971) <i>Comment</i> : S,dS. H (1-4 MeV) -> Si.	1971-Chem 1634
1971	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. 'Energy Loss of H, D, and 4He Ions Channeled through Thin Single Crystals of Silicon' <i>Phys. Rev. Letters</i> , 27, 1194-96 (1971) <i>Comment</i> : S. 0.9-5.0 MeV H, D, He -> Si Cryst. And Amorph.	1971-Dell 0132
1972	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. 'Indirect Determination of the Energy Loss of Protons Channeled in Silicon Crystals' <i>Rendiconti Della Academia Nazionale Dei Lincei. Classe Di Scienze Fisiche Matematiche E Naturali. Ser. 8,</i> , 52, No. 5, P. 727-33 (1972) <i>Comment</i> : S. 1600 keV H -> Si (Cryst.)	1972-Dell 0463
1972	Foster, C. Kool, W. H. VanDerWeg, W. F. Roosendaal, E. 'Random Stopping Power for Protons in Silicon' <i>Rad. Effects</i> , 16, 139-40 (1972) <i>Comment</i> : S. 120 keV H -> Si	1972-Fost 0466
1972	Sone, K. Fukusawa, F. 'Transmission of Fast Protons through Si Single Crystals' <i>Mem Fac. Eng. Kyoto Univ.</i> , 34, 325-32 (1972) <i>Comment</i> : S, dS. 3 MeV H -> Si (Cryst.)	1972-Sone 0693

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<b>1973</b>	Bottiger, J. Eisen, F. H. 'On Conversion from an Energy Scale to a Depth Scale in Channeling Experiments' <i>Thin Solid Films, 19, 239-246 (1973)</i> <i>Comment : S. 0.2-0.4 MeV H -&gt; Si (Cryst.)</i>	<b>1973-Bott</b> 0507
<b>1974</b>	Bulgakov, Yu. V. Nikolaev, V. S. Shulga, V. I. 'The Experimental Determination of the Impact Parameter Dependence of Inelastic Energy Loss of Channeled Ions' <i>Phys. Letters A, 46, 477-78 (1974)</i> <i>Comment : S, dS. 1.15, 1.75 MeV H, 5.7 MeV N -&gt; Si (Cryst.)</i>	<b>1974-Bulg</b> 0668
<b>1975</b>	DellaMea, G. Drigo, A. V. LoRusso, S. Mazzoldi, P. Bentini, G. G. 'Transmission Energy Loss of Protons Channeled in Thin Silicon Single Crystals of Medium Energy' <i>Datz, B. R. Appleton, C. D. Moak (Ed.): Atomic Collisions in Solids. Plenum N. Y., 75-76 (1975)</i> <i>Comment : S. 50-300 keV H -&gt; Si (Cryst.) Chann. To Random Ratio</i>	<b>1975-Dell</b> 0574
<b>1975</b>	Eisen, F. H. Bottiger, J. 'Transmission Energy Spectra of Channeled Protons Scattered in Thin Silicon Films' <i>Atomic Collisions in Solids, Plenum Press, 919-27 (1975)</i> <i>Comment : S,dS. 200, 400 keV H -&gt; Si (Cryst.)</i>	<b>1975-Eise</b> 0579
<b>1975</b>	Gotz, V. G. Klinge, K. D. Schwabe, F. 'Measurement of the Energy Loss in Thin Silicon Single Crystals' <i>Exp. Tech. Phys., 23, 167-169 (1975)</i> <i>Comment : S. 0.7-1.6 MeV H -&gt; Si</i>	<b>1975-Gotz</b> 1017
<b>1975</b>	Gotz, G. Klinge, K. D. Finger, U. 'A Combination of Dechanneling and Energy Measurements of Protons in Thin Silicon Single Crystals.' <i>Atomic Collisions in Solids, Plenum Press, 693-716 (1975)</i> <i>Comment : S. 0.7-1.8 MeV H -&gt; Si (Cryst.) Chann. To Random Ratio.</i>	<b>1975-Gotz2</b> 0577
<b>1975</b>	Melvin, J. D. 'Energy Loss of Light Ions Channeling in Silicon' <i>Ph.D., Cal. Inst. Tech., Unpublished (1975)</i> <i>Comment : S, dS. 0.5-1.6 MeV H -&gt; Si (110), (111), (211)</i>	<b>1975-Melv</b> 1271
<b>1975</b>	Melvin, J. D. Tombrello, T. A. 'Energy Loss of Low Energy Protons Channeling in Silicon Crystals' <i>Rad. Effects, 26, 113-26 (1975)</i> <i>Comment : S. 0.5-1.6 MeV H -&gt; Si (Cryst.)</i>	<b>1975-Melv2</b> 0757

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<b>1976</b>	Grahmann, G. Kalbitzer, S. 'Nuclear and Electronic Stopping Powers of Low Energy Ions with $Z \leq 10$ in Silicon' <i>Nucl. Inst. Methods, 132, 119-23 (1976)</i> <i>Comment : S. 2-60 keV H, He, B, C, N, Ne -&gt; Si</i>	1976-Grah 0871
<b>1976</b>	Ligeon, E. Guivarc'H, A. 'Hydrogen Implantation in Silicon Between 1.5 - 60 keV.' <i>Rad. Effects, 27, 129-37 (1976)</i> <i>Comment : S,R,dR. 1.5-60 keV H -&gt; Si. S. 1.5-60 keV H, 2.0 MeV 11B -&gt; Si</i>	1976-Lige 0817
<b>1977</b>	Cembali, F. Zignani, F. 'Determination of Random and Aligned Stopping Powers for 80-300 keV Protons in Silicon by Backscattering Measurements' <i>Rad. Effects, 31, 169-173 (1977)</i> <i>Comment : S. 80-300 keV H -&gt; Si Single Crystal ([110], [100], [111], and Random)</i>	1977-Cemb 1033
<b>1977</b>	Thompson, D. A. Robinson, J. E. Walker, R. S. 'Inelastic Stopping of Medium Energy Light Ions in Silicon' <i>Rad. Effects, 32, 169-175 (1977)</i> <i>Comment : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -&gt; Si</i>	1977-Thom 1076
<b>1978</b>	Carnera, A. Della Mea, G. Drigo, A. V. Lo Russo, S. Mazzoldi, P. 'Channeled and Random Proton Stopping Power in Si in the 300-1000 keV Energy Range' <i>Phys. Rev. B, 17, 3492 (1978)</i> <i>Comment : S. H (40-900 keV) -&gt; Si. Channeled and Random stopping powers.</i>	1978-Carn 1631
<b>1978</b>	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. 'Channeling of Fast Protons, Deuterons and Alpha Particles' <i>Preprint (1978)</i> <i>Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -&gt; Si</i>	1978-Jarv 1148
<b>1979</b>	Jarvis, O. N. Sherwood, A. C. Whitehead, C. Lucas, M. W. 'Channeling of Fast Protons, Deuterons, and Alpha Particles' <i>Phys. Rev. B, 19, 5559-5577 (1979)</i> <i>Comment : S, R, dR. 160 keV He, 81.5 keV D, 158.5 keV H -&gt; Si</i>	1979-Jarv 1199
<b>1980</b>	Izmailov, Sh. Z. Sirotnin, E. I. Tulinov, A. F. 'Energy Loss of Protons in Si, Ge, and Mo' <i>Nucl. Inst. Methods, 168, 81-84 (1980)</i> <i>Comment : S, dS. .1-1 MeV H -&gt; Si, Ge, Mo</i>	1980-Izma 1342
<b>1981</b>	Kuhr, E. Lenkeit, K. Taubner, F. 'Measurements of the Stopping Power of 40-300 keV Protons in Silicon' <i>Phys. Stat. Sol. A, 66, 131 (1981)</i> <i>Comment : S. H (40-300 keV) -&gt; Si</i>	1981-Kuhr 1694

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<b>1981</b>	Pearce, J. D. Hart, R. R. 'Stopping Power Measurements in the 20-150 keV Region using Thick Target Backscattering: H and He on C, Si and Au' <i>J. Appl. Phys.</i> , 52, 5056 (1981) <i>Comment</i> : S. H, He (20-150 keV) -> C, Si, Au	<b>1981-Pear</b> 1736
<b>1981</b>	Santry, D. C. Werner, R. D. 'Stopping Powers of C, Al, Si, Ti, Ni, Ag and Au for Deuterons' <i>Nucl. Inst. Methods</i> , 188, 211 (1981) <i>Comment</i> : S. D (0.2-2.0 MeV) -> C, Al, Si, Ti, Ni, Ag, Au	<b>1981-Sant</b> 1756
<b>1983</b>	Hancock, S. James, F. Movchet, J. Rancoita, P. G. Van Rossum, L. 'Energy Loss and Energy Straggling of Protons and Pions in the Momentum Range 0.7-115 GeV/c' <i>Phys. Rev. A</i> , 28, 615 <i>Comment</i> : S,dS. H, pions (0.7-115 GeV/c) -> Si	<b>1983-Hanc</b> 1659
<b>1984</b>	Sirotnin, E. I. Tulinov, A. F. Khodyrev, V. A. Mizgulin, V. N. 'Proton Energy Loss in Solids' <i>Nucl. Inst. Methods</i> , B4, 337 (1984) -1 <i>Comment</i> : S. H (0.1-6.0 MeV) -> Al, Si, Sc, V, Cu, Zn, Ga, Ge, Y, Zr, Nb, Mo, Ag, Cd, In, Sn, La, Sm, Gd, Yb, Hf, Ta, W, Pt, Au, Pb	<b>1984-Siro</b> 1770
<b>1985</b>	Gehrmann, P. Lenkeit, K. Stolle, R. 'Measurement of Proton Channeling Energy Losses in Silicon in the Intermedicate Energy Region' <i>Phys. Stat. Sol. B</i> , 131, 519 (1985) <i>Comment</i> : S. H (40-350 keV) -> Si. Channeled stopping powers.	<b>1985-Gehr</b> 1963
<b>1988</b>	Mertens, P. Bauer, P. 'Reference Stopping Cross Sections for 30-600 keV Protons in Silicon' <i>Nucl. Inst. Methods</i> , B33, 133 (1988) <i>Comment</i> : S. H (30-600 keV) -> Si	<b>1988-Mert</b> 1720
<b>1990</b>	Bauer, P. 'Stopping Power of Light Ions near the Maximum' <i>Nucl. Inst. Methods</i> , B45, 673 (1990) <i>Comment</i> : S. H, H- (30-700 keV) -> C, Al, Si, Ni, Cu, Ag, Au, SiO2, HC2, Al2O3	<b>1990-Baue</b> 1608
<b>1991</b>	Medenwaldt, R. Moller, S. P. Uggerhoj, E. Worn, T. Hvelplund, P. 'Measurement of the Stopping Power of Silicon for Antiprotons between 0.2 - 3 MeV' <i>Nucl. Inst. Methods</i> , B58, 1-5 (1991) <i>Comment</i> : S. H-( 0.2-3 MeV) -> Si Anti-proton stopping powers.	<b>1991-Mede</b> 1716

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<b>1992</b>	Bichsel, H. Hiraoka, T. 'Energy Loss of 70 MeV Protons in Elements' <i>Nucl. Inst. Methods, B66, 345-351 (1992)</i> <i>Comment : S. H (70 MeV) -&gt; C, H2O, SiO2, Al, Si, Ti, Cr, Fe, Co, Ni, Cu, Zn, Zr, Nb, Mo, Ag, Cd, In, Sn, Ta, W, Pb</i>	<b>1992-Bich2</b> 1624
<b>1993</b>	Narumi, K. Fujii, Y. Kishine, K. Fujiwara, S. Kimura, K. 'Energy Losses of 12-32 keV H, He and N Ions at Glancing Angle Scattering from Clean Surfaces of Silicon Crystals' <i>J. Phys. Soc. Jap., 62, 1603-1611 (1993)</i> <i>Comment : S. H, He, N (12-32 keV) -&gt; Si Surface scattering effects</i>	<b>1993-Naru</b> 2054
<b>1994</b>	Avdeichikov, V. V. Bergholt, L. Guttormsen, M. Taylor, J. E. Westerberg, L. 'Light Output and Energy Resolution of CsI, YAG, GSO, BGO, LSO Scintillators for Light Ions' <i>Nucl. Inst. Methods, A349, 216-224 (1994)</i> <i>Comment : S. H, D, He (3-20 MeV/amu)-&gt; CsI, YAG, GSO, BGO, LSO Scintillators</i>	<b>1994-Avde</b> 2074
<b>1995</b>	Shevchenko, V. A. 'Stopping Power Measurements of Low Energy Protons using Backscattering on the Target' <i>Metall-Novei.-Tekh., 17, 27-29 (1995) Translated in "Physics of Metals"</i> <i>Comment : S. H (80-240 keV) -&gt; Si, Cd, Fe, Au, YBaCuO</i>	<b>1995-Shev</b> 2378
<b>1996</b>	Ikeda, A. Sumitomo, K. Nishioka, T. Kido, Y. 'Stopping Powers and Energy Straggling for 50-300 keV H in Amorphous Si and Ge Films' <i>Nucl. Inst. Methods, B115, 34-38 (1996)</i> <i>Comment : S, dS. H (50-300 keV) -&gt; Si, Ge</i>	<b>1996-Iked</b> 2029
<b>1996</b>	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods' <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> <i>Comment : S. Light ions -&gt; Si, GaAs (channeled)</i>	<b>1996-Misd</b> 0964
<b>1996</b>	Niemann, D. Kinac, G. Kalbitzer, S. 'Stopping Power of H, He and N in Si in the Energy Range of 0.02-1.0 MeV/amu' <i>Nucl. Inst. Methods, 118, 11-18 (1996)</i> <i>Comment : S. H, He, N (.02-1.0 MeV/amu) -&gt; Si</i>	<b>1996-Niem</b> 1101
<b>1997</b>	Moller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. 'Direct Measurements of the Stopping Power for Antiprotons of Light and Heavy Targets' <i>Phys. Rev. A, 56, 2930-2939 (1997)</i> <i>Comment : S. H- (50 - 700 keV) -&gt; Al, Si, Ti, Cu, Ag, Ta, Pt, Au</i>	<b>1997-Moll</b> 2364

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<b>1997</b>	Muller, S. P. Uggerhoj, E. Bluhme, H. Knudsen, H. Mikkelsen, U. 'Measurement of the Barkas Effect Around the Stopping Power Maximum for Light and Heavy Targets' <i>Nucl. Inst. Methods, B122, 162-166 (1997)</i> <i>Comment : S. H- (50-700 keV) -&gt; Si, Au</i>	<b>1997-Mull</b> 2026
<b>2002</b>	Fama, M. Lantschner, G. H. Eckardt, J. C. Arista, N. R. Gayone, J. E. 'Energy Loss and Angular Dispersion of 2-200 keV Protons in Amorphous Silicon' <i>Nucl. Inst. Methods, B193, 91-96 (2002)</i> <i>Comment : S. H -&gt; Si(amor)</i>	<b>2002-Fama</b> 3129
<b>2006</b>	Hobler, G. Bourdelle, K. K. Akatsu, T. 'Random and Channeling Stopping Power of H in Si below 100 keV' <i>Nucl. Inst. Methods, B242, 617-619 (2006)</i> <i>Comment : S. H -&gt; Si (Rand. &amp; Chan.)</i>	<b>2006-Hobl</b> 3118
<b>2008</b>	Abdesselam, M. Ouichaoui, S. Azzouz, M. Chami, A.C. Siad, M. 'Stopping of 0.3-1.2 MeV/u protons and alpha particles in Si' <i>Nucl. Instrum. Methods Phys. Res. B 266, 3899 (2008)</i> <i>Comment : S. H, He (0.3-1.2 MeV/u) -&gt; Si</i>	<b>2008-Abde</b> 3150
<b>2009</b>	Barradas, N.P. Alves, E. Siketic, Z. Bogdanovic, I. Radovic, 'Stopping power of different ions in Si measured with a bulk sample method and Bayesian inference data analysis ' <i>AIP Conf. Proc. 1099, 331 (2009)</i> <i>Comment : S. H (0-2500 keV), Li (0-3000 keV) -&gt;Si</i>	<b>2009-Barr</b> 3151